

Supplementary Materials

Plasma Enhanced Atomic Layer Deposition of Plasmonic TiN Ultrathin Films Using TDMATi and NH₃

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Supplementary Information

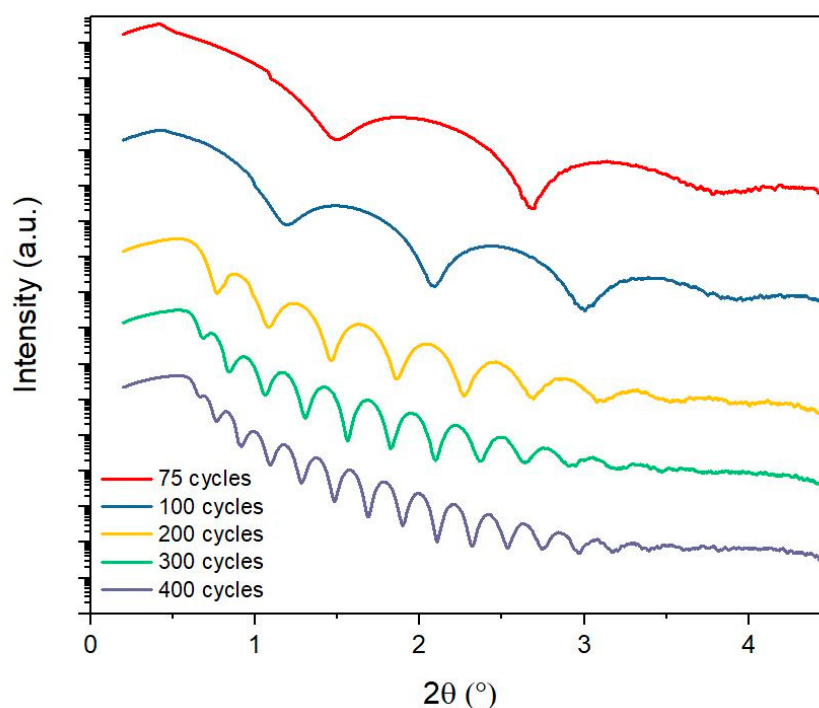


Figure S1. Raw XRR data of TiN films on Si (100) with varying cycle number.

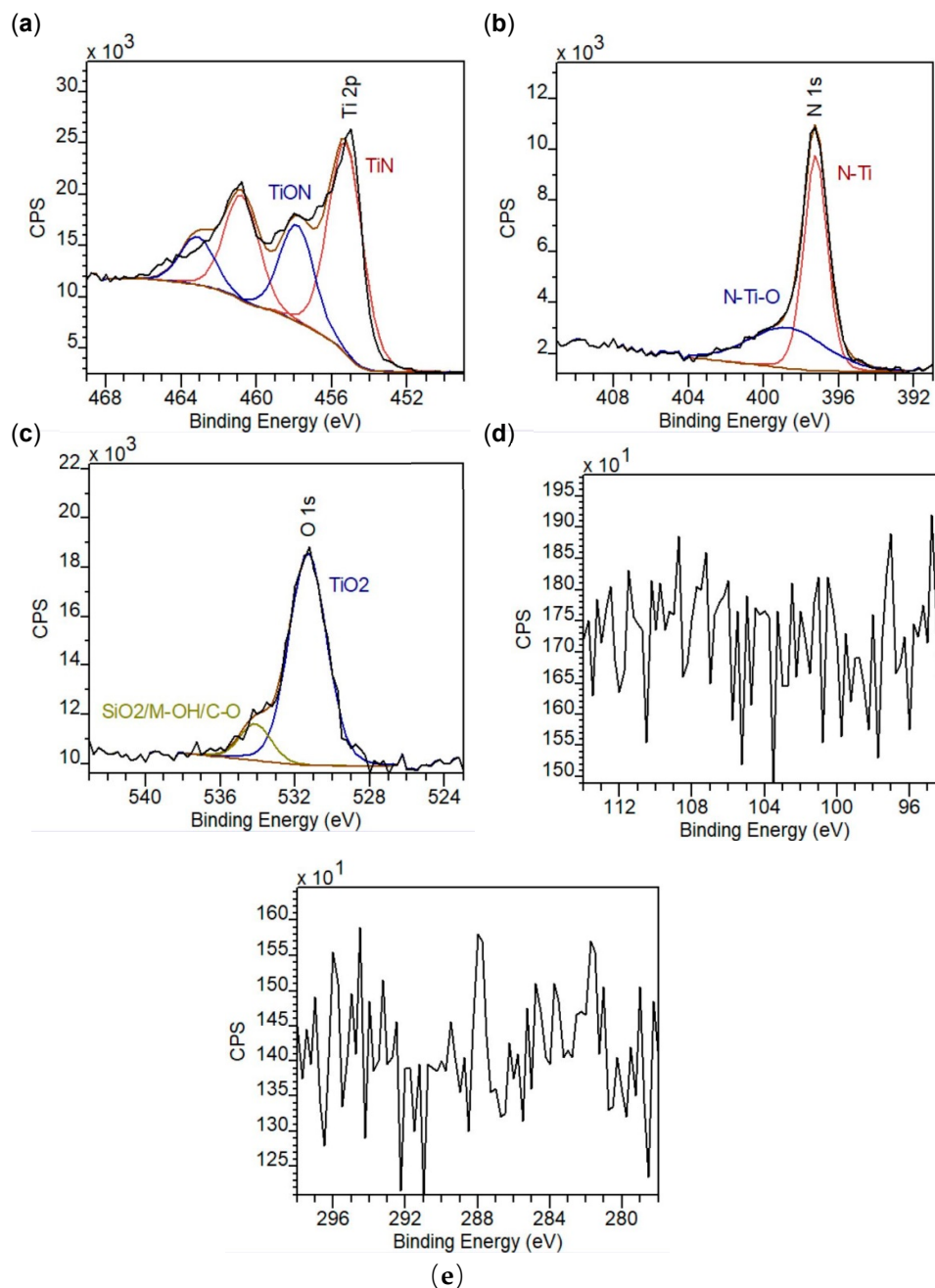


Figure S2. Structural characterization of 100 ALD cycles TiN on Si after H₂ post-deposition treatment using XPS (a) titanium 2p region, (b) nitrogen 1s region, (c) oxygen 1s region, (d) silicon 2p region, and (e) carbon 1s region.

